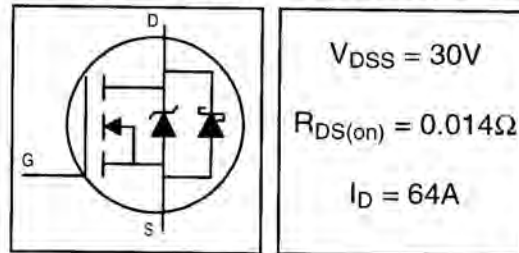


IRL3103D1PbF

FETKY™ MOSFET & SCHOTTKY RECTIFIER

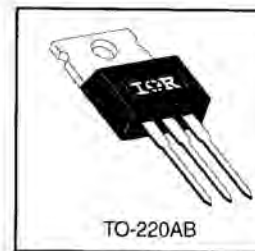
- Copackaged HEXFET® Power MOSFET and Schottky Diode
- Generation 5 Technology
- Logic Level Gate Drive
- Minimize Circuit Inductance
- Ideal For Synchronous Regulator Application
- Lead-Free



Description

The FETKY family of copackaged HEXFET power MOSFETs and Schottky Diodes offer the designer an innovative board space saving solution for switching regulator applications. A low on resistance Gen 5 MOSFET with a low forward voltage drop Schottky diode and minimized component interconnect inductance and resistance result in maximized converter efficiencies.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ③	64	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ③	45	
I_{DM}	Pulsed Drain Current ①③	220	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_C = 25^\circ C$	Power Dissipation	89	W
	Linear Derating Factor	0.56	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
T_J	Operating Junction and	-55 to + 150	
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	°C
	Mounting torque, 6-32 or M3 screw	10 lb•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	62	

MOSFET Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.037	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⓐ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.014 0.019	Ω	$V_{GS} = 10V, I_D = 34A$ ⓑ $V_{GS} = 4.5V, I_D = 28A$ ⓑ
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	23	—	—	S	$V_{DS} = 25V, I_D = 32A$ ⓐ
I_{DSS}	Drain-to-Source Leakage Current	—	—	0.10 22	mA	$V_{DS} = 30V, V_{GS} = 0V$ $V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	43	nC	$I_D = 32A$
Q_{gs}	Gate-to-Source Charge	—	—	14	nC	$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	23	nC	$V_{GS} = 4.5V$, See Fig. 6 ⓐ
$t_{d(on)}$	Turn-On Delay Time	—	9.0	—	ns	$V_{DD} = 15V$ $I_D = 32A$ $R_G = 3.4\Omega, V_{GS} = 4.5V$ $R_D = 0.43\Omega$, ⓐⓑ
t_r	Rise Time	—	210	—		
$t_{d(off)}$	Turn-Off Delay Time	—	20	—		
t_f	Fall Time	—	54	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1900	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 0V$
C_{oss}	Output Capacitance	—	810	—		
C_{rss}	Reverse Transfer Capacitance	—	240	—		
C_{iss}	Input Capacitance	—	3500	—		



Body Diode & Schottky Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_F (AV)	(Schottky)	—	—	2.0	A	MOSFET symbol showing the integral reverse p-n junction and Schottky diode.
I_{SM}	Pulsed Source Current (Body Diode) ⓐ	—	—	220		
V_{SD1}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 32A, V_{GS} = 0V$ ⓐ
V_{SD2}	Diode Forward Voltage	—	—	0.50	V	$T_J = 25^\circ\text{C}, I_S = 1.0A, V_{GS} = 0V$ ⓐ
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 25^\circ\text{C}, I_F = 32A$
Q_{rr}	Reverse Recovery Charge	—	49	73	nC	$di/dt = 100A/\mu s$ ⓐ
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

ⓐ Repetitive rating; pulse width limited by max. junction temperature. (See fig. 10)

ⓑ Uses IRL3103 data and test conditions

Ⓒ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

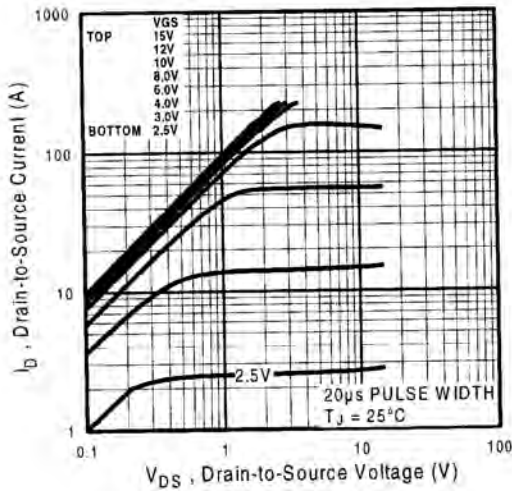


Fig 1. Typical Output Characteristics

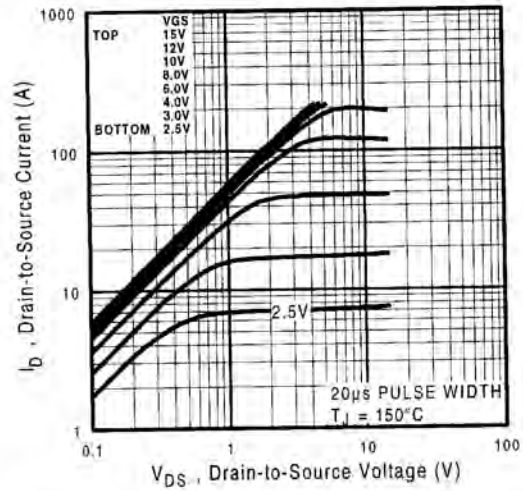


Fig 2. Typical Output Characteristics

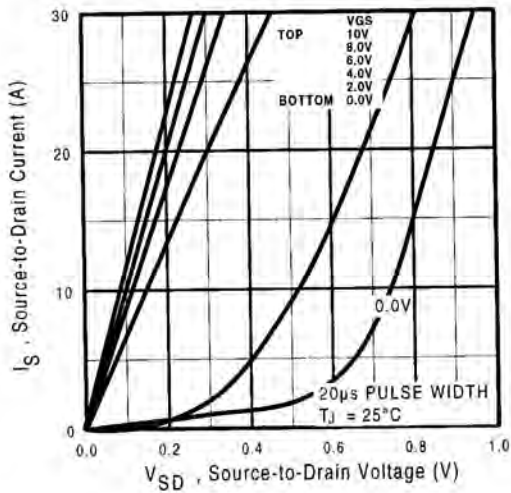


Fig 3. Typical Reverse Output Characteristics

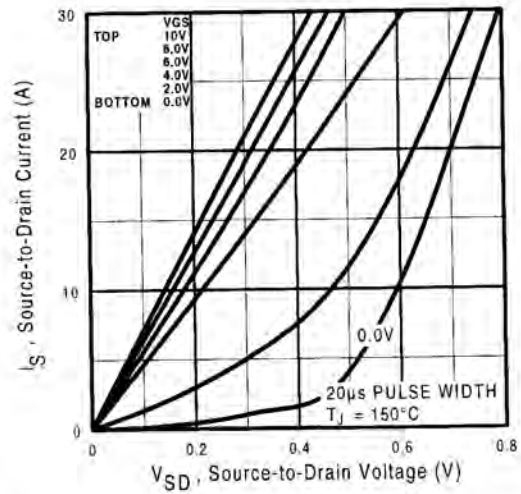


Fig 4. Typical Reverse Output Characteristics

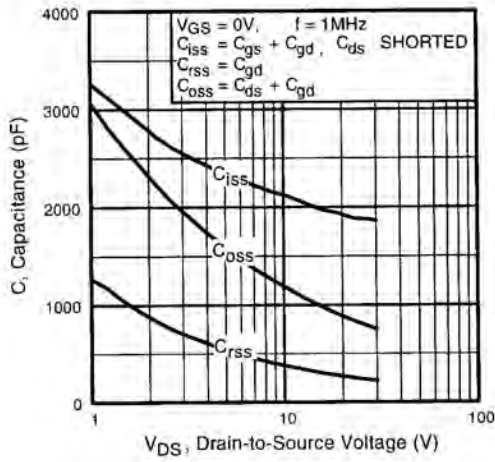


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

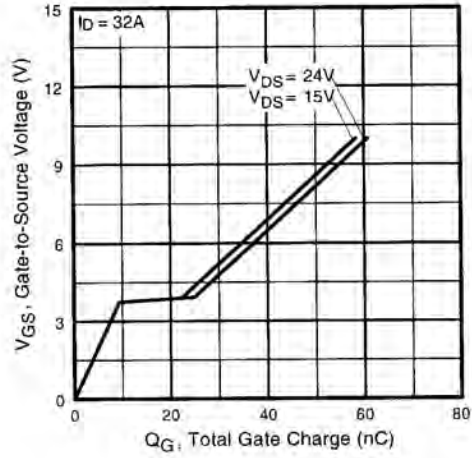


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

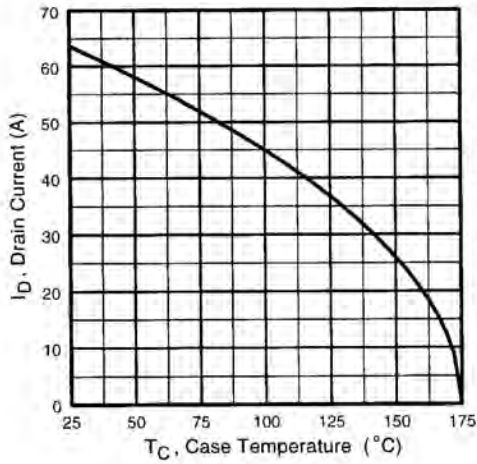


Fig 7. Maximum Drain Current Vs. Case Temperature

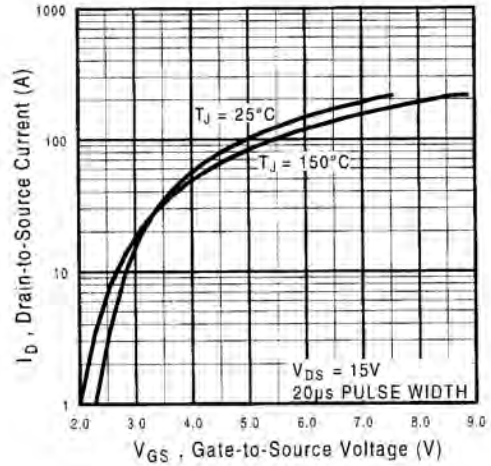


Fig 8. Typical Transfer Characteristics

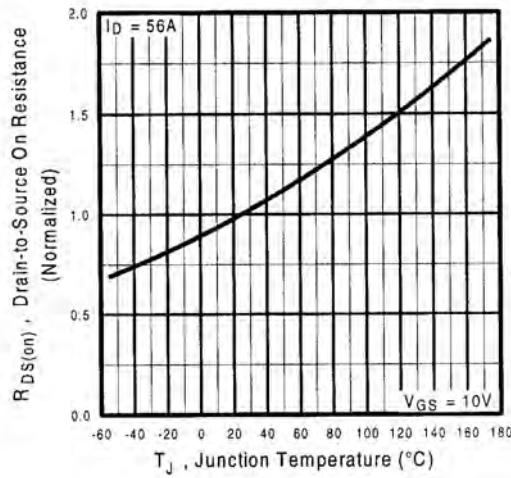


Fig 9. Normalized On-Resistance Vs. Temperature

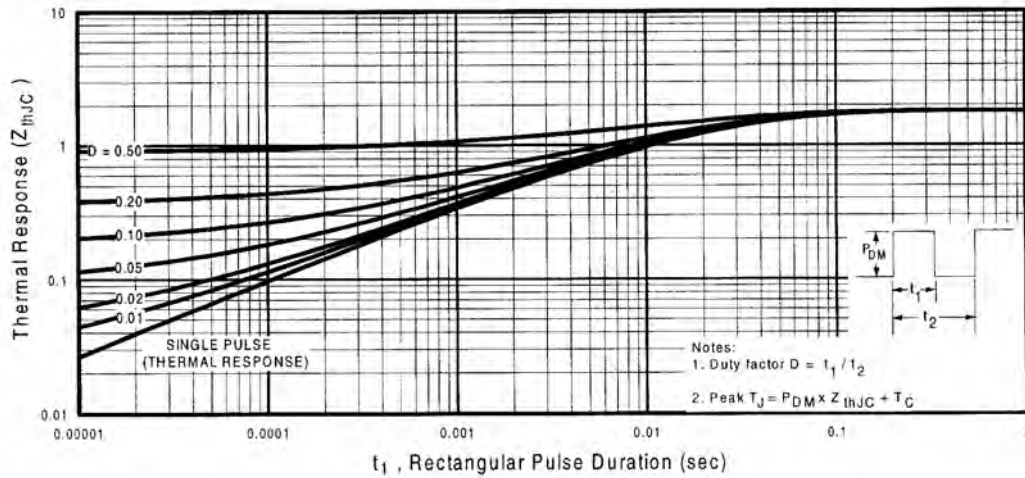


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>